

Supplementary File

Omnidirectional and broadband antireflection effect with tapered silicon nanostructures fabricated with low-cost and large-area-capable nanosphere lithography process

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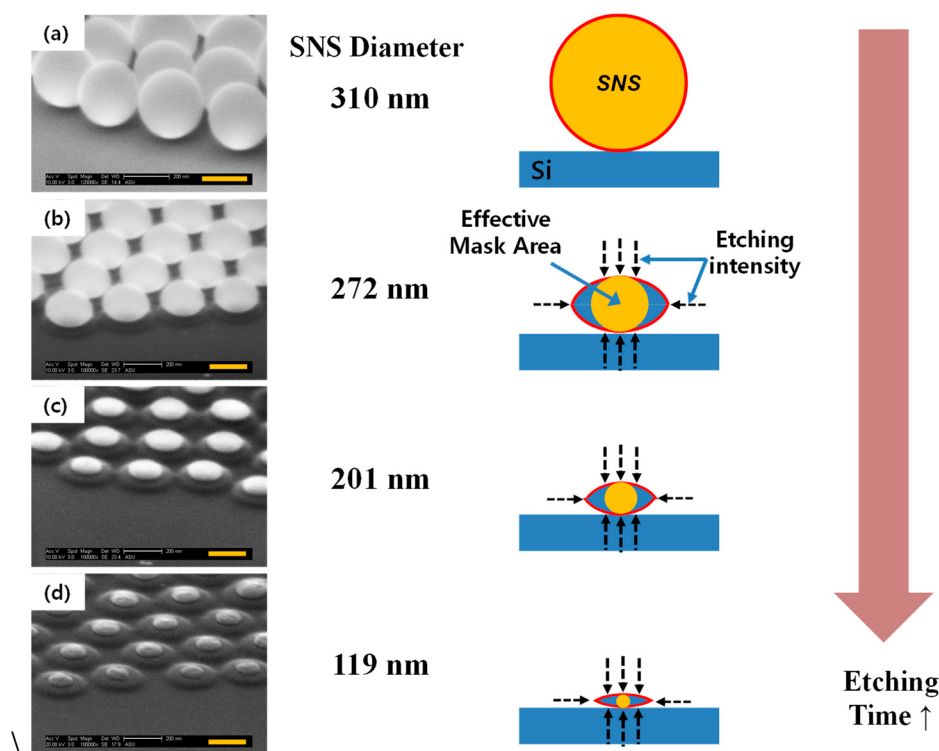


Figure S1. SNS mask size and shape change with increasing CHF_3/Ar etching time.

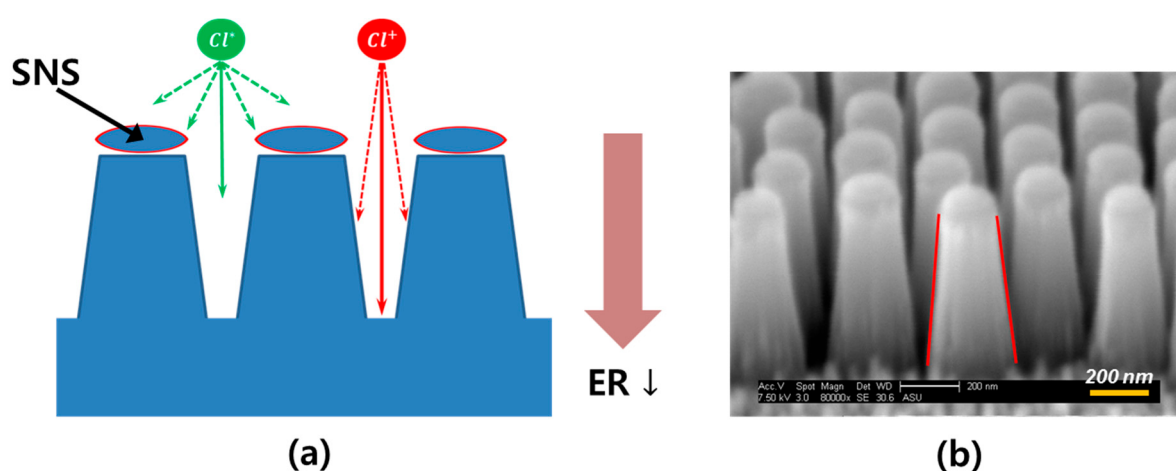


Figure S2. (a) Schematic illustration on aspect-ratio-dependent etching (ARDE) originated from fewer etching species reaching the bottom of high-aspect-ratio Si NPs followed by reduced ER and (b) 5-min Cl_2 etched sample with 201 nm SNS mask size.



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